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ABSTRACT OF THE DISCLOSURE

A metal thin film of a semiconductor device and method for forming the same is disclosed, in which excellent step coverage and surface roughness are maintained. The metal thin film of a semiconductor device according to the present invention includes: a barrier metal layer formed on a semiconductor substrate; and a PVD seed thin film, a CVD thin film, and a PVD reflow thin film sequentially formed on the barrier metal layer, wherein the PVD seed thin film, the CVD thin film and the PVD reflow thin film are of the same material.

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